



UPDATE CHANGE NOTIFICATION #16450B

Generic Copy

Issue Date: 27-Mar-2012

TITLE: Fabrication Site Transfer. ON Semiconductor's wafer Fab (CZ4) in Roznov, Czech Republic is now qualified to process the RELAY DRIVERS as shown below. These RELAY DRIVERS parts are currently fabricated at ON Semiconductor's Aizu Japan Wafer Fab.

PROPOSED FIRST SHIP DATE: 15-Jul-2012

AFFECTED CHANGE CATEGORY(S): ON Semiconductor Fab Site

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or <blanca.kruse@onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office

ADDITIONAL RELIABILITY DATA:

Contact your local ON Semiconductor Sales Office or <laura.rivers@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

This update is a follow up from FPCN #16450B. ON Semiconductor is notifying customers that the Aizu to CZ4 transfer of the following RELAY DRIVER products, is now fully qualified. Upon expiration of the associated Final PCN(s), all devices will be supplied from the CZ4 wafer Fab in Roznov, Czech Republic. No die design, process, or electrical parameters changes occurred as a result of this qualification.

*Due to priorities around the Aizu fabrication transfer, the Au wire to Cu wire conversion is being dropped from the scope at this time and will be readdressed at a later date."



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RELIABILITY DATA SUMMARY:

Full qualification and reliability testing was performed on the NUD3160LT1G in the SOT23 pkg and the NUD3160DMT1G in the SC74 package. The qualification vehicles were chosen to fully represent the entire Relay Driver family.

Reliability Test Results:

Package: SOT23

NUD3160LT1G

Test:	Conditions:	Interval:	Results
HTRB	Tj=150C,80% Rated Voltage	1008 hrs	0/168
Autoclave+PC	Ta=121C RH=100% ~15 psig	96 hrs	0/84
H3TRB+PC	Ta=85C RH=85%	1008 hrs	0/84
	bias=80% rated V or100V Max		
TC+PC	Ta= -65 C to 150 C	1000 cyc	0/84
RSH	Ta=260C, 10 sec dwell		0/30
HTSL	Ta=150C	1008 hrs	0/84
HTGB	Ta=150C, 100% Gate V	1008 hrs	0/84
IOL	Ta=25C, delta Tj=100C, Ton=Toff= 0.5mS Relay G8TB-1A-64	1008 hrs	0/80

Package: SC74

NUD3160DMT1G

Test:	Conditions:	Interval:	Results
HTRB	Tj=150C,80% Rated Voltage	1008 hrs	0/336
Autoclave+PC	Ta=121C RH=100% ~15 psig	96 hrs	0/168
H3TRB+PC	Ta=85C RH=85%	1008 hrs	0/168
	bias=80% rated V or100V Max		
TC+PC	Ta= -65 C to 150 C	1000 cyc	0/168
RSH	Ta=260C, 10 sec dwell		0/60
HTSL	Ta=150C	1008 hrs	0/168
HTGB	Ta=150C, 100% Gate V	1008 hrs	0/168
IOL	Ta=25C, delta Tj=100C, Ton=Toff= 0.5mS Relay G8N-1-DC12	1008 hrs	0/328

ELECTRICAL CHARACTERISTIC SUMMARY:

Datasheet specifications and product electrical performance will remain unchanged. Additional data is available upon request. Contact Blanca Kruse < blanca.kruse@onsemi.com >



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CHANGED PART IDENTIFICATION:

Affected products from ON Semiconductor with date code starting WW30 (2012) and greater will be sourced from the CZ4 Wafer fab in Roznov, Czech Republic.

List of affected General Parts:

NUD3160DMT1G
NUD3160LT1G
SZNUD3160LT1G
SZNUD3160DMT1G
NUD3124DMT1G
NUD3124LT1G
SZNUD3124LT1G
SZNUD3124DMT1G
NUD3105DMT1G
NUD3105LT1G
NUD3112DMT1G
NUD3112LT1G